

Features

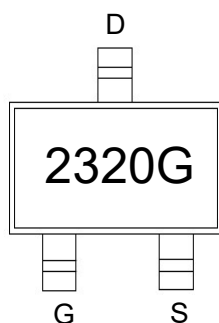
- Trench Power LV MOSFET technology
- High Power and current handing capability

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
20V	15mΩ@4.5V	6.8A
	18mΩ@2.5V	

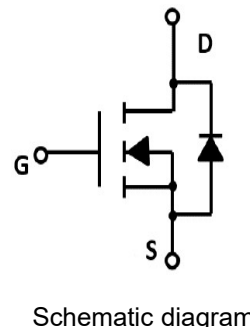
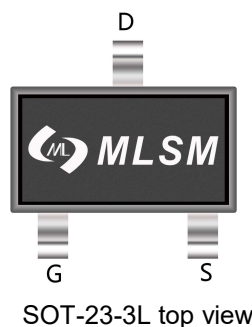
Application

- Load Switch for Portable Applications



2320G: Device code

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		20	V
V _{GS}	Gate-Source Voltage		±12	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	6.8	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	30	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	6.8	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	1.5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		313	°C/W

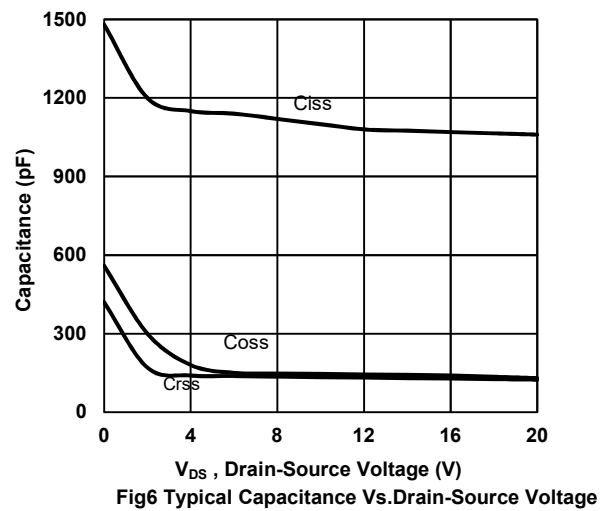
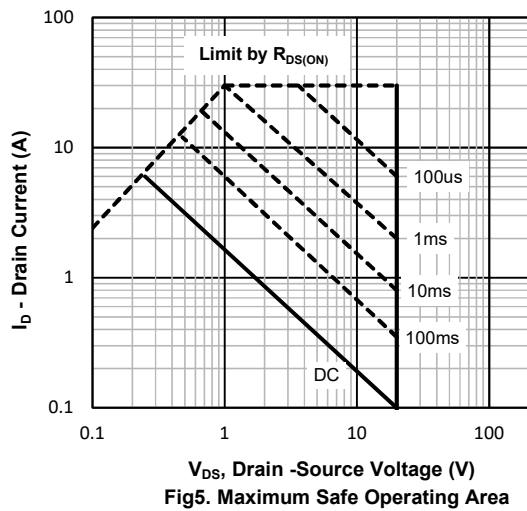
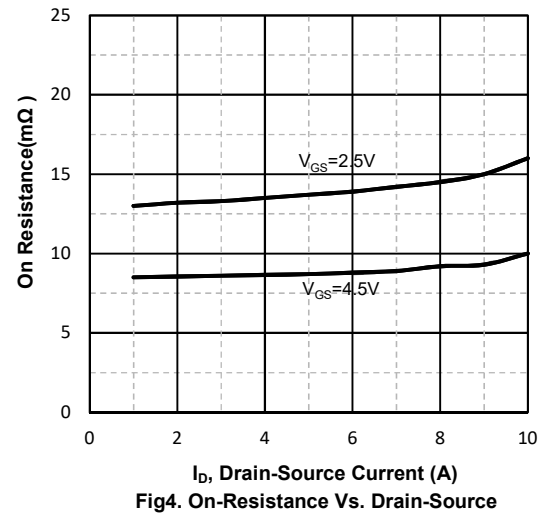
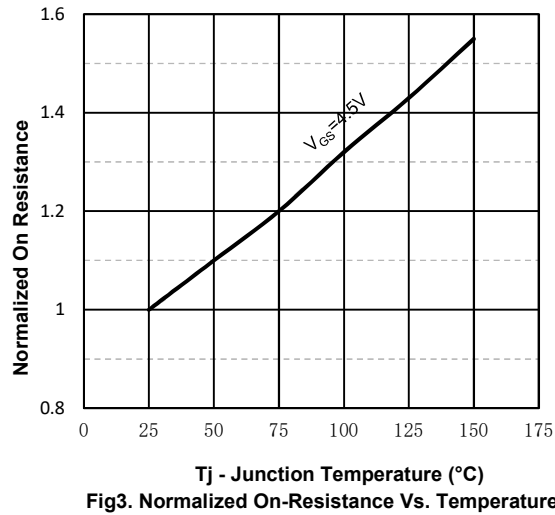
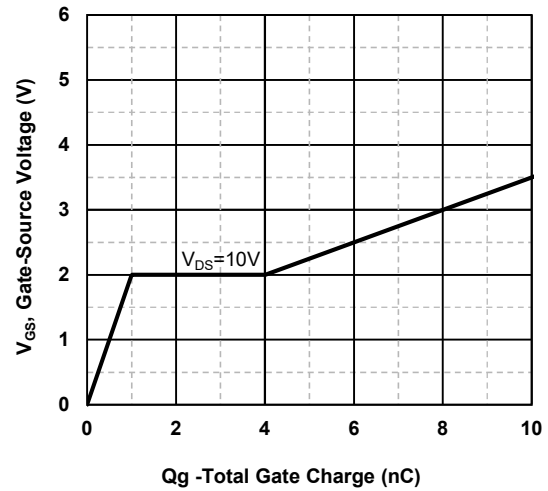
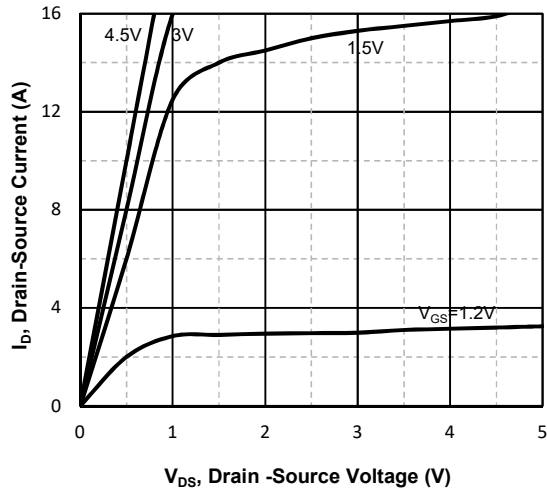
Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSK2320G	SOT-23-3L	2320G	3,000	45,000	180,000	7"reel

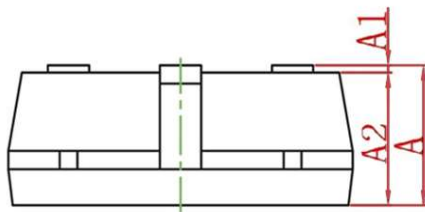
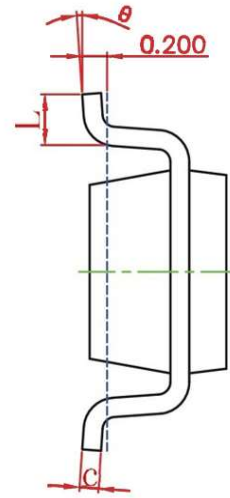
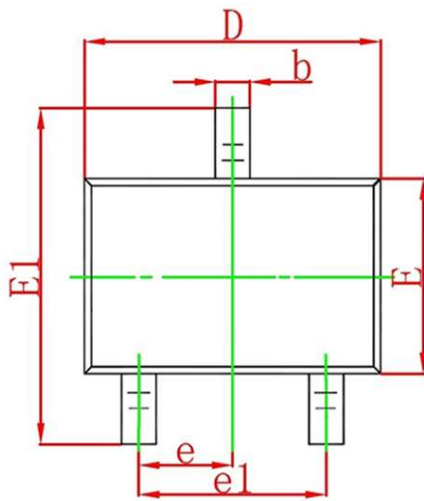
Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =6.8A	--	8.5	15	mΩ
		V _{GS} =2.5V, I _D =3.0A	--	13	18	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	1150	--	pF
C _{OSS}	Output Capacitance		--	185	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	145	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =6A, V _{GS} =4.5V	--	15	--	nC
Q _{gs}	Gate Source Charge		--	0.8	--	nC
Q _{gd}	Gate Drain Charge		--	3.2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =6A, V _{GS} =4.5V, R _G =6Ω	--	6	--	nS
t _r	Turn-on Rise Time		--	13	--	nS
t _{d(off)}	Turn-Off Delay Time		--	52	--	nS
t _f	Turn-Off Fall Time		--	16	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=6.8A	--	--	1.2	V

Typical Operating Characteristics



SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°